
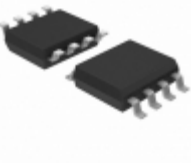






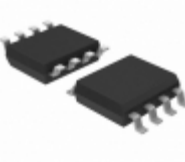
	<p>SI4162DY-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI4162DY-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 19.3A 8-SOIC</p> <p>Datenblätter:  SI4162DY-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 49719 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI4162DY-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 30V 19.3A 8-SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	49719 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SO
Verlustleistung (max)	2.5W (Ta), 5W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	19.3A (Tc)
Rds On (Max) @ Id, Vgs	7.9 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	30nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1155pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Original-Reel®












































SI4162DY-T1-GE3 ist neu im Original, Suche SI4162DY-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4162DY-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI4162DY-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI4164DY-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 30A 8-SOIC</p>	 <p>SI4160DY-T1-GE3 VISHAY SI4160DY-T1-GE3 VISHAY</p>	 <p>SI4164DY-T1-E3 IOR SI4164DY-T1-E3 IOR</p>	 <p>SI4162DY-T1-E3 VISHAY SI4162DY-T1-E3 VISHAY</p>
 <p>SI4162DY-T1 VISHAY VISHAY SO-8</p>	 <p>SI4162DY VISHAY SI4162DY VISHAY</p>	 <p>SI4160DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 25.4A 8-SOIC</p>	 <p>SI4162DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 19.3A 8-SOIC</p>

heiße Teile

Mehr

 SI4134DY-T1-GE3	 SI4134DY-T1-GE3	 SI4134DY-T1-GE3	 SI4134T-BMR	 SI4134T-GMR
 SI4136-F-GM	 SI4136-F-GMR	 SI4136DY-T1-GE3	 SI4136DY-T1-GE3	 SI4136XM-BT
 SI4136XM-GTR	 SI4154DY-T1-GE3	 SI4154DY-T1-GE3	 SI4156DY	 SI4156DY-T1-E3
 SI4156DY-T1-GE3	 SI4156DY-T1-GE3	 SI4160DY	 SI4160DY-T1-E3	 SI4160DY-T1-GE3
 SI4160DY-T1-GE3	 SI4160DY-T1-GE3	 SI4162DY	 SI4162DY-T1-E3	 SI4162DY-T1-GE3
 SI4164DY	 SI4164DY-T1-E3	 SI4164DY-T1-GE3	 SI4164DY-T1-GE3	 SI4166DY
 SI4166DY-T1-E3	 SI4166DY-T1-GE3	 SI4166DY-T1-GE3	 SI4168DY	 SI4168DY-T1-E3
 SI4168DY-T1-GE3	 SI4168DY-T1-GE3	 SI4170DY-T1-GE3	 SI4170DY-T1-GE3	 SI4172DY
 SI4172DY-T1-E3	 SI4172DY-T1-GE3	 SI4172DY-T1-GE3	 SI4174DY	 SI4174DY-T1-E3
 SI4174DY-T1-GE3	 SI4174DY-T1-GE3	 SI4176DY-T1-GE3	 SI4176DY-T1-GE3	 SI4178DY

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